

What is claimed is:

1. A polishing composition comprising:
silica;
a nitrogen-containing alkaline compound; and
5 hydrogen peroxide,
wherein the nitrogen-containing alkaline compound is
basic amino acid,
a content of the hydrogen peroxide is more than 0% by
mass and less than 0.03% by mass with respect to the total
10 mass of the polishing composition,
the electrical conductivity is 0.05 mS/cm or more and
0.25 mS/cm or less, and
a pH exceeds 9.
- 15 2. The polishing composition according to claim 1, wherein
the content of hydrogen peroxide is 0.0027% by mass or more
and less than 0.03% by mass.
3. The polishing composition according to claim 1, wherein
20 the content of hydrogen peroxide is more than 0% by mass and
0.02% by mass or less.
4. The polishing composition according to claim 3, wherein
the content of hydrogen peroxide is more than 0% by mass and
25 less than 0.01% by mass.
5. The polishing composition according to any one of claims
1 to 4, wherein the pH is 10.0 or higher and 11 or less.
- 30 6. The polishing composition according to any one of claims
1 to 5, wherein the polishing composition consists of the
silica; the basic amino acid; the hydrogen peroxide, and a
dispersing medium.

7. The polishing composition according to any one of claims
1 to 6, which is used for polishing an object to be polished
containing polycrystalline silicon which is not doped with
5 impurities and polycrystalline silicon which is doped with
n-type impurities.

8. A polishing method comprising: polishing an object to
be polished using the polishing composition according to any
10 one of claims 1 to 6.

9. A method of producing a semiconductor substrate,
comprising:
polishing a semiconductor substrate containing
15 polycrystalline silicon which is not doped with impurities
and polycrystalline silicon which is doped with n-type
impurities with the polishing method according to claim 8.